



安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

SD101AWS-SD101CWS

SOD-323 Schottky Barrier Rectifier Diode 肖特基势垒整流二极管

SOD-323

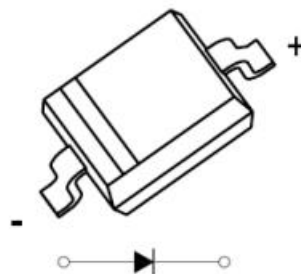
■Features 特点

Fast switching time 快速开关时间

Low forward voltage drop 低正向压降

Surface mounted device 表面贴装器件

Case 封装:SOD-323



■Maximum Rating 最大额定值

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	SD101AWS	SD101BWS	SD101CWS	Unit 单位
Device Marking 产品印字		S1	S2	S3	
Peak Reverse Voltage 反向峰值电压	V_{RRM}	60	50	40	V
DC Reverse Voltage 直流反向电压	V_R	60	50	40	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	42	35	28	V
Forward Rectified Current 正向整流电流	I_F	15			mA
Peak Surge Current 峰值浪涌电流	I_{FSM}	2			A
Power Dissipation 耗散功率	P_D	200			mW
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	500			$^{\circ}\text{C}/\text{W}$
Junction Temperature 结温	T_J	125			$^{\circ}\text{C}$
Storage Temperature 储藏温度	T_{stg}	-50to+150			$^{\circ}\text{C}$

■Electrical Characteristics 电特性

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	SD101AWS	SD101BWS	SD101CWS	Unit 单位	Condition 条件
Reverse Voltage 反向电压	V_R	60	50	40	V	$I_R=10\mu\text{A}$
Forward Voltage 正向电压	V_F	0.41 1	0.4 0.95	0.39 0.9	V	$I_F=1\text{mA}$ $I_F=15\text{mA}$
Reverse Current 反向电流	I_R	0.2			μA	$V_R=V_{RRM}$
Reverse Recovery Time 反向恢复时间	T_{rr}	1			nS	$I_F=I_R=5\text{mA}$ $I_{rr}=0.5\text{mA}$
Diode Capacitance 二极管电容	C_T	2			pF	$V_R=1\text{V}, f=1\text{MHz}$

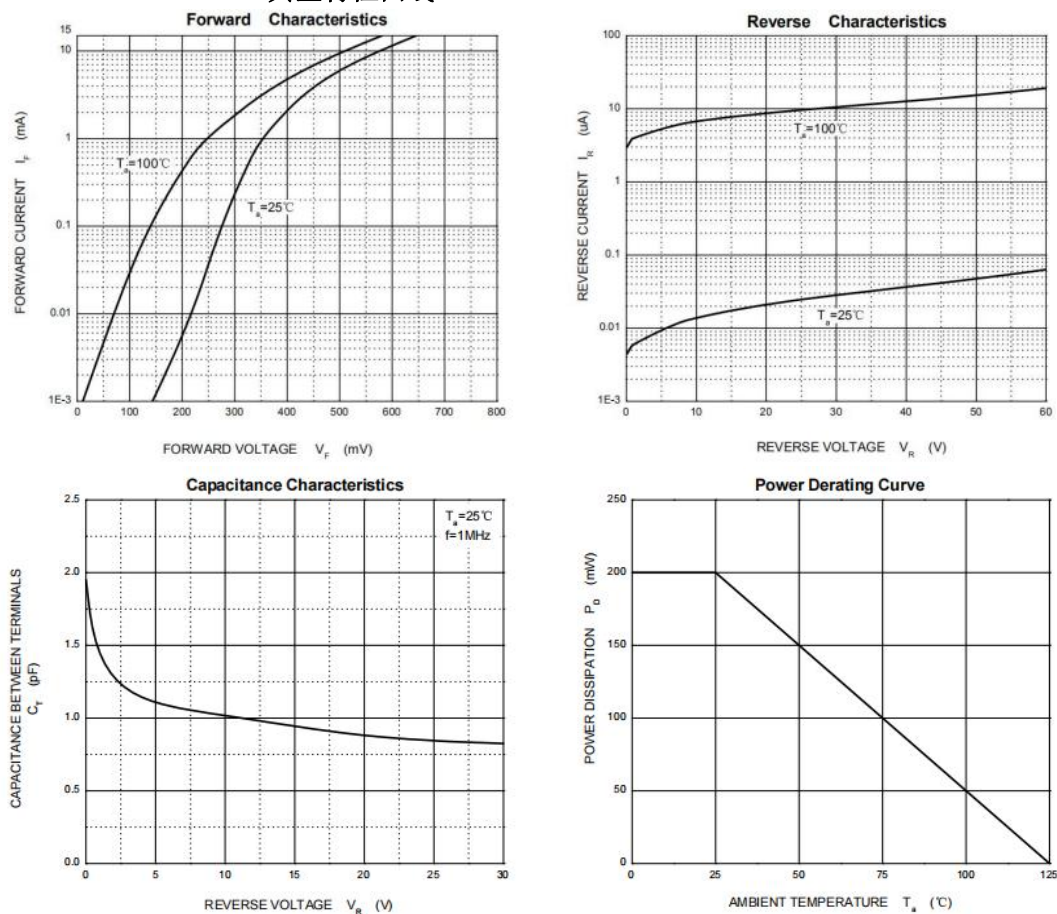


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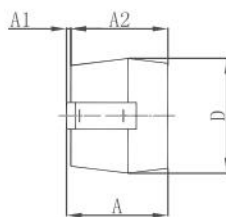
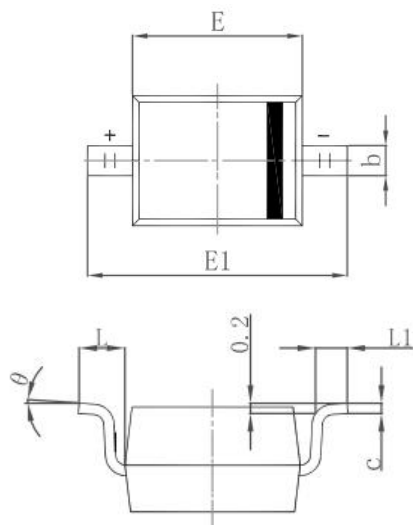
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Typical Characteristic Curve 典型特性曲线



Dimension 外形封装尺寸 SOD-323



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A		1.100		0.043
A1	0.000	0.100	0.000	0.004
A2	0.800	1.000	0.031	0.039
b	0.250	0.350	0.010	0.014
c	0.080	0.150	0.003	0.006
D	1.200	1.400	0.047	0.055
E	1.600	1.800	0.063	0.071
E1	2.500	2.750	0.098	0.108
L	0.475 REF		0.019 REF	
L1	0.250	0.400	0.010	0.016
θ	0 $^\circ$	8 $^\circ$	0 $^\circ$	8 $^\circ$